

N-channel 650 V, 0.425  $\Omega$  typ., 11 A MDmesh™ II Power MOSFET  
in DPAK, TO-220FP, I<sup>2</sup>PAKFP and TO-220 packages

Datasheet - production data

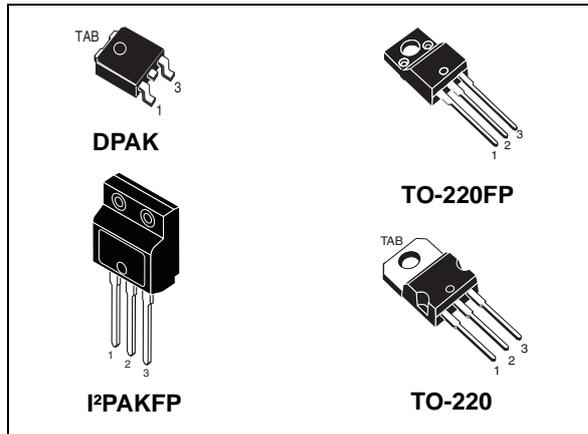
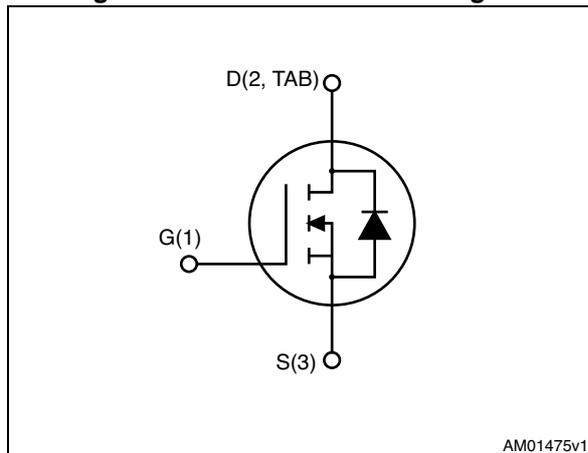


Figure 1. Internal schematic diagram



## Features

Order codes	$V_{DSS} @ T_{Jmax}$	$R_{DS(on) max}$	$I_D$
STD11NM65N	710 V	< 0.455 $\Omega$	11 A
STF11NM65N			
STFI11NM65N			
STP11NM65N			

- 100% avalanche tested
- Low input capacitance and gate charge
- low gate input resistance

## Applications

- Switching applications

## Description

These devices are N-channel Power MOSFETs developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order codes	Marking	Packages	Packaging
STD11NM65N	11NM65N	DPAK	Tape and reel
STF11NM65N		TO-220FP	Tube
STFI11NM65N		I <sup>2</sup> PAKFP	
STP11NM65N		TO-220	